

## FX6ASJ-03

# High-Speed Switching Use Pch Power MOS FET

REJ03G0247-0200 Rev.2.00 Nov 21, 2006

#### **Features**

• Drive voltage: 4 V

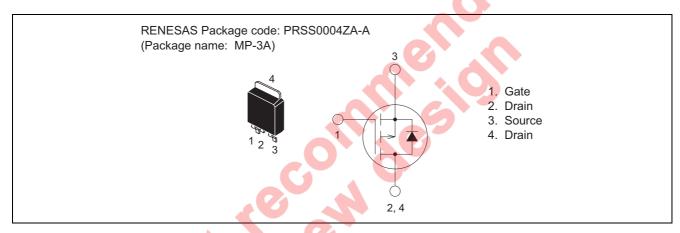
•  $V_{DSS}$ : -30 V

•  $r_{DS(ON) (max)}$ : 0.29  $\Omega$ 

•  $I_D: -6 A$ 

• Recovery Time of the Integrated Fast Recovery Diode (TYP.): 40 ns

#### **Outline**



### **Applications**

Motor control, lamp control, solenoid control, DC-DC converters, etc.

### **Maximum Ratings**

 $(Tc = 25^{\circ}C)$ 

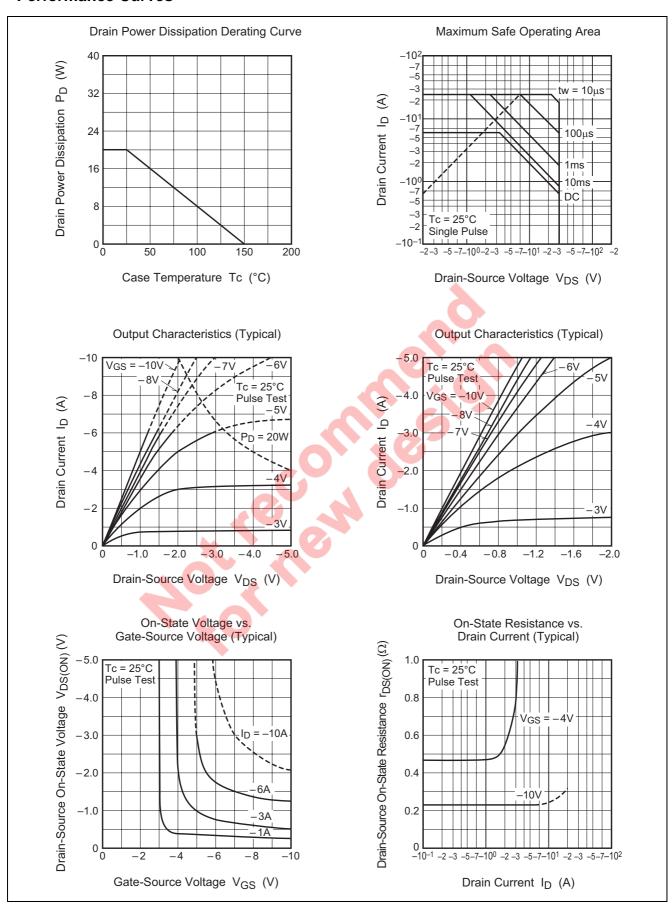
Parameter	Symbol	Ratings	Unit	Conditions
Drain-source voltage	V <sub>DSS</sub>	-30	V	V <sub>GS</sub> = 0 V
Gate-source voltage	V <sub>GSS</sub>	±20	V	V <sub>DS</sub> = 0 V
Drain current	I <sub>D</sub> -6		А	
Drain current (Pulsed)	I <sub>DM</sub>	-24	А	
Avalanche current (Pulsed)	I <sub>DA</sub>	-6	А	L = 30 μH
Source current	Is	-6	А	
Source current (Pulsed)	I <sub>SM</sub>	-24	А	
Maximum power dissipation	P <sub>D</sub>	20	W	
Channel temperature	Tch	- 55 to +150	°C	
Storage temperature	Tstg	- 55 to +150	°C	
Mass	_	0.32	g	Typical value

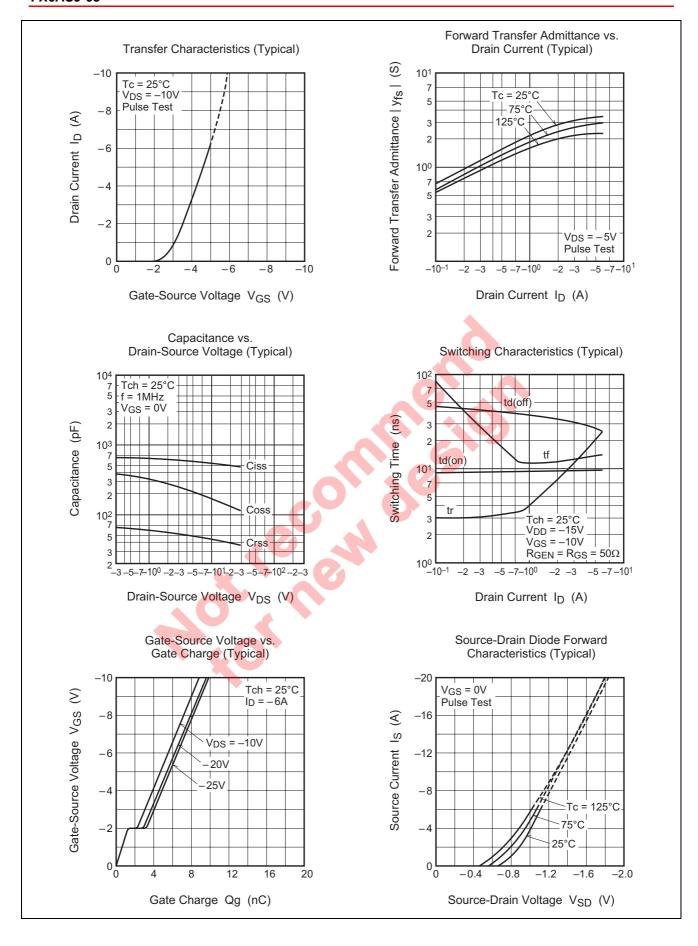
### **Electrical Characteristics**

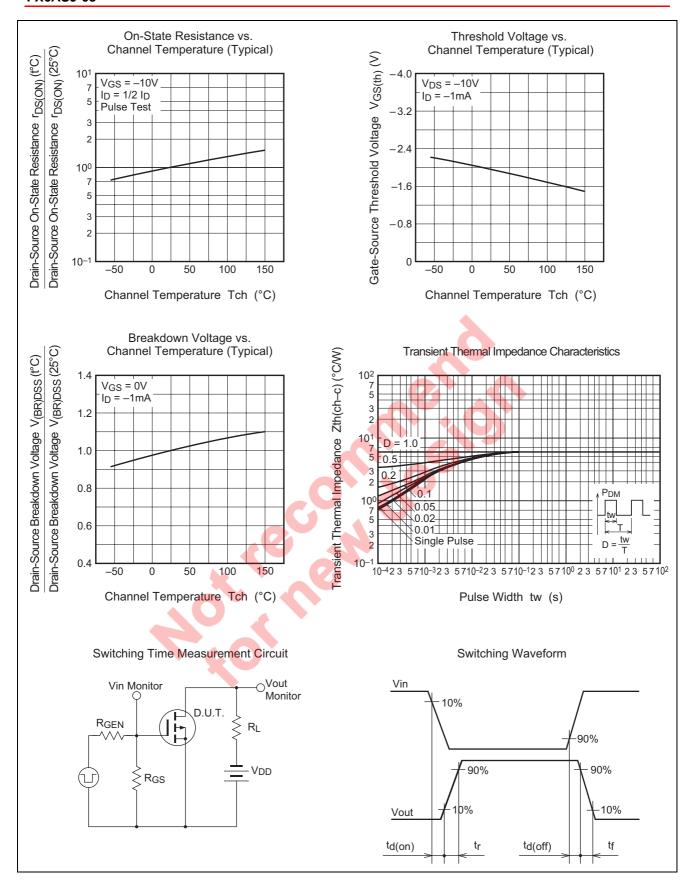
 $(Tch = 25^{\circ}C)$ 

Drain-source breakdown voltage Gate-source leakage current	V <sub>(BR)DSS</sub>					
Gate-source leakage current	(511)500	-30	_	_	V	$I_D = -1 \text{ mA}, V_{GS} = 0 \text{ V}$
	I <sub>GSS</sub>	_	_	±0.1	μΑ	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$
Drain-source leakage current	I <sub>DSS</sub>	_	_	-0.1	mA	$V_{DS} = -30 \text{ V}, V_{GS} = 0 \text{ V}$
Gate-source threshold voltage	V <sub>GS(th)</sub>	-1.3	-1.8	-2.3	V	$I_D = -1 \text{ mA}, V_{DS} = -10 \text{ V}$
Drain-source on-state resistance	r <sub>DS(ON)</sub>	_	0.23	0.29	Ω	$I_D = -3 \text{ A}, V_{GS} = -10 \text{ V}$
Drain-source on-state resistance	r <sub>DS(ON)</sub>	_	0.46	0.62	Ω	$I_D = -1 A$ , $V_{GS} = -4 V$
Drain-source on-state voltage	V <sub>DS(ON)</sub>	_	- 0.69	- 0.87	V	$I_D = -3 \text{ A}, V_{GS} = -10 \text{ V}$
Forward transfer admittance	y <sub>fs</sub>	_	2.6	_	S	$I_D = -3 \text{ A}, V_{DS} = -5 \text{ V}$
Input capacitance	Ciss	_	550	_	pF	$V_{DS} = -10 \text{ V}, V_{GS} = 0 \text{ V},$
Output capacitance	Coss	_	165	_	pF	f = 1MHz
Reverse transfer capacitance	Crss	_	45	_	pF	
Turn-on delay time	t <sub>d(on)</sub>	_	9	_	ns	$V_{DD} = -15 \text{ V}, I_D = -3 \text{ A},$
Rise time	t <sub>r</sub>	_	14	_	ns	$V_{GS} = -10 \text{ V},$
Turn-off delay time	t <sub>d(off)</sub>	_	32	_	ns	$R_{GEN} = R_{GS} = 50 \Omega$
Fall time	t <sub>f</sub>	_	14	_ (	ns	
Source-drain voltage	V <sub>SD</sub>	_	-1.0	-1.5	V	$I_S = -3 \text{ A}, V_{GS} = 0 \text{ V}$
Thermal resistance	Rth(ch-c)	_	_	6.25	°C/W	Channel to case
Reverse recovery time	t <sub>rr</sub>	_	40	VA	ns	$I_S = -3 \text{ A}, \text{ dis/dt} = 50 \text{ A/}\mu\text{s}$
Not lecondesion						

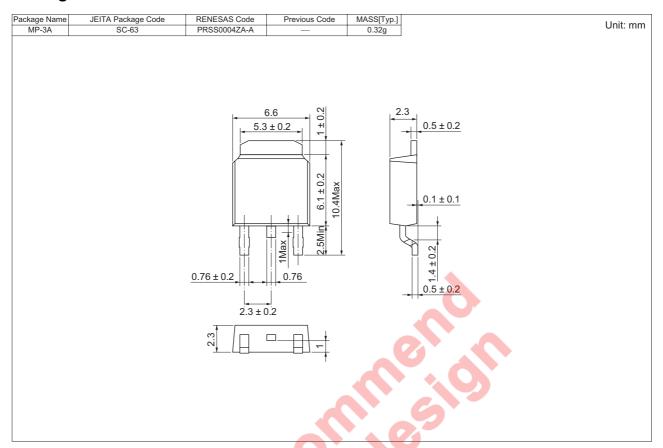
#### **Performance Curves**







### **Package Dimensions**



### **Order Code**

Lead form	Standard packing	Quantity	Standard order code	Standard order code example
Surface-mounted type	Taping	3000	Type name – T +Direction (1 or 2) +3	FX6ASJ-03-T13
Surface-mounted type	Plastic Magazine (Tube)	75	Type name	FX6ASJ-03

Note: Please confirm the specification about the shipping in detail.

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